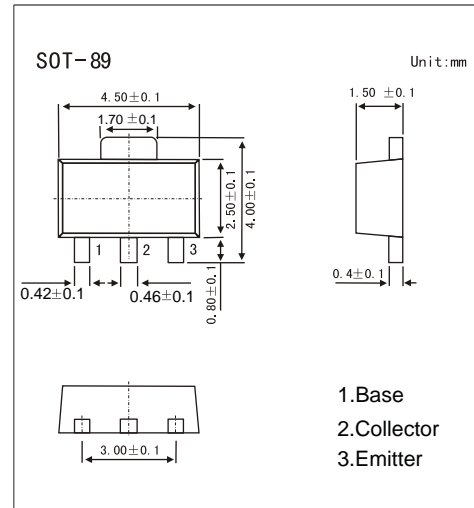


PNP Transistors

2SB772

■ Features

- PNP transistor High current output up to 3A
- Low Saturation Voltage
- Complement to 2SD882



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V _{CB0}	-40	V
Collector to Emitter Voltage	V _{CEO}	-30	V
Emitter to Base Voltage	V _{EBO}	-6	V
Collector Current to Continuous	I _c	-3	A
Collector Dissipation	P _c	1.0	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c =-100uA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{CEO}	I _c = -10 mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{EBO}	I _E = -100 uA, I _c =0	-6			V
Collector cut-off current	I _{CB0}	V _{CB} =-40 V, I _E =0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _c =0			-1	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _c = -1A	60		400	
		V _{CE} =-2V, I _c = -100mA	32			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-2A, I _B =- 0.2A			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c =-2A, I _B = -0.2A			-1.5	V
Transition frequency	f _T	V _{CE} =-5 V, I _c =-0.1mA, f = 10MHz	50			MHz

■ Classification of h_{fe}(1)

Type	2SB772-R	2SB772-Q	2SB772-P	2SB772-E
Range	60-120	100-200	160-320	200-400
Marking	772R	772Q	772P	772E

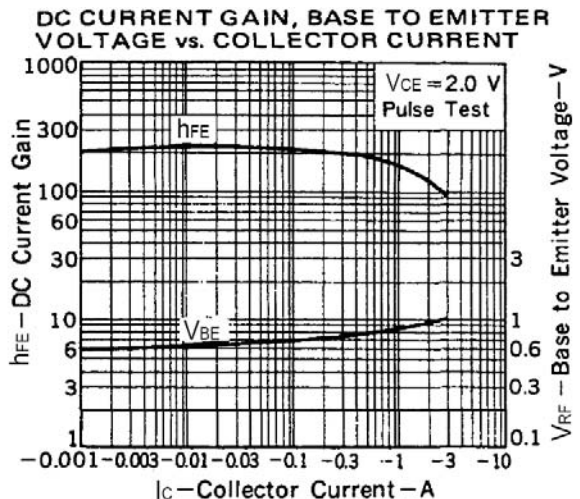
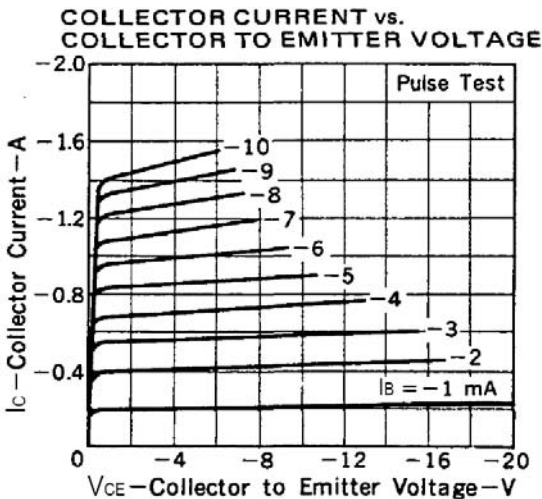
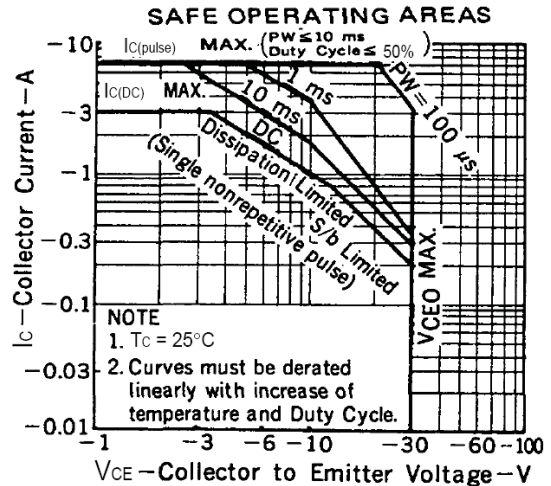
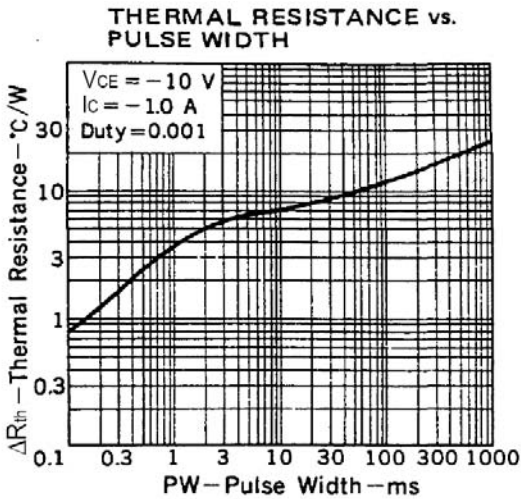
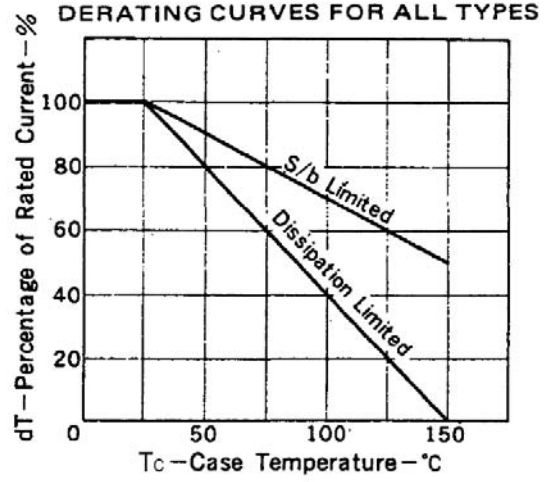
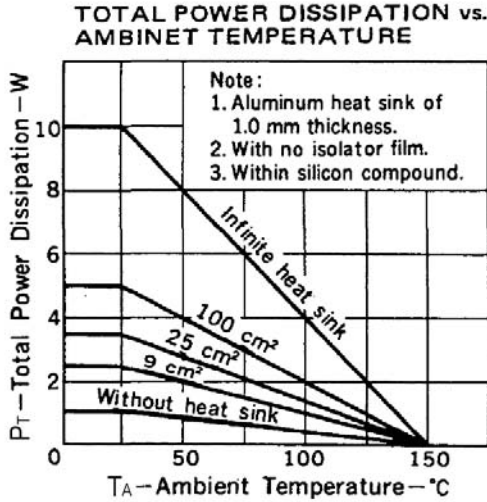


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SMD Type Transistors

2SB772

Typical Characteristics





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